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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of Christopher L. Chua et al.

Group Art Unit: 2828

Application No.: 09/933,960

Examiner: James A. Menefee

Filed: August 20, 2001

Confirmation No.: 9309

For: METHOD AND STRUCTURE FOR ELIMINATING POLARIZATION INSTABILITY IN Laterally - OXIDIZED VCSELS

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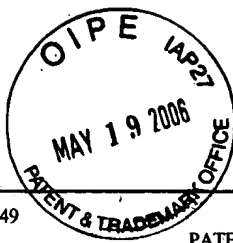
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09/933,960

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

APPLICANT(S)
Robert L. THORNTONFILING DATE
August 20, 2001GROUP
2828

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